On the K ondo e ect in carbon nanotubes at half hal ng

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Abstract

In a single state of a quantum dot the K ondo e ect arises due to the spin-degeneracy, which is present if the dot is occupied with one electron (N = 1). The eigenstates of a carbon nanotube quantum dot possess an additional orbital degeneracy leading to a four-fold shell pattern. This additional degeneracy increases the possibility for the K ondo e ect to appear. We revisit the K ondo problem in m etallic carbon nanotubes by linear and non-linear transport m easurem ent in this regime, in which the four-fold pattern is present. We have analyzed the ground state of C N T s, which were grown by chemical vapor deposition, at llings N = 1, N = 2, and N = 3. O fparticular interest is the half-led shell, i.e. N = 2. In this case, the ground state is either a paired electron state or a state for which the singlet and triplet states are electively degenerate, allowing in the latter case for the appearance of the K ondo elect. We deduce numbers for the elective m issmatch

of the levels from perfect degeneracy and the exchange energy J. W hile 0:1 0:2 (in units of level spacing) is in agreement with previous work, the exchange term is found to be surprisingly small: J. 0:02. In addition we report on the observation of gaps, which in one case is seen at N = 3 and in another is present over an extended sequence of levels.

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I. IN TRODUCTION

In the past decade, transport m easurem ents have em erged as a prim ary tool for exploring the electrical properties of structures on the nanom eter scale. D ue to their unique electronic bandstructure, m uch attention has been focused on carbon nanotubes (CNTs).¹ Form etallic single wall carbon nanotubes (SW NTs) just two spin degenerate one-dimensional (1d) m odes should govern their transport properties at low energies, which m akes them interesting m odel system s to explore the physics in reduced dimensions.²

Due to the nite length, given by the lithographically fabricated contacts on opposite sides of the CNT (two-term inaldevice with source and drain contacts), the one-dimensional CNT is turned into a quantum dot³ at low temperatures (typically at . 10K), i.e. into a zero-dimensional object with a discrete level spectrum. The connement is formed by the nite back-rejection at the edges of the contacts. The level spacing E is determined by the contact separation L and is inversely proportional to it. This particle in the box-m odel holds provided the level-broadening and the temperature are both smaller than E.

Until now, three transport regimes have been identied in SWNTs: A) single-electron tunneling,⁴ which is dominated by the on-site Coulomb repulsion expressed by the energy term $U = e^2 = C$, where C is the total capacitance; B) the regime of correlated transport, in which higher-order tunneling processes, are appreciable, leading to the emergence of the K ondo e ect;^{5,6} and C) the open SW NT for which C oulom b interaction m ay be neglected and the residual gate-dependence of G can be described as in a tunable Fabry-Perot resonator.⁷ A) holds for low, B) for interm ediate and C) for high transparent contacts. The K ondoe ect, which occurs at interm ediate contact transparency, can be seen as the Holly G rail of many electron physics. It has rst been observed in quantum dots by Goldhaber-Gordon et al.⁵ and in CNTs by Nycard et al.⁸ In contrast to the Coulomb Blockade (CB) regime, which only probes the electrons con ned on a QD, the K ondo e ect incorporates delocalized electrons in the leads coherently. The presence of a degenerate ground state in the quantum dot (for example, a singly occupied level with two-fold degeneracy due to the spin degree of freedom) form s the basis for the K ondo e ect. A multitude of coherent second- and higherorder elastic tunneling processes between the Ferm i seas of the leads and the quantum -dot state are enabled, leading to the appearance of a narrow peak in the density of states

(DOS) right at the Ferm i level (the K ondo resonance) at su ciently low temperatures. Its width is given by the K ondo temperature T_K which measures the binding energy of this many-electron state. The peak in the DOS enhances the probability for electrons to tunnel from source to drain. As a consequence the zero-temperature linear-conductance saturates at the quantized conductance $G_0 = 2e^2 = h$ (unitary limit), provided the device is coupled symmetrically to source and drain.

As in atom s, eigenstates in quantum dots (QD s) may be degenerate due to symmetries and together with the spin degeneracy and Pauli principle lead to the formation of electronic shells. Indeed, striking shell patterns have been observed in QD s.^{9,10} The eigenstates (Bloch-states) at the Ferm i energy of graphene (two-dimensional sheet of graphite) is two fold degenerate. The two wave functions correspond to the two carbon sublattices (the unit-cell is composed of two C-atom s). This degeneracy is preserved in CNTs and should therefore lead to two degenerate orbitals in a nite-length nanotube in 0d. Together with the spin degeneracy, the shells are expected to be four-fold degenerate. This shell pattern has recently been observed by Buitelaar and coworkers¹¹ in multi-wall carbon nanotubes (MWNTs) and by Liang et al. in SWNTs.¹³ W ithin one shell the ground-state spin was shown to follow the sequence S = 0 ! 1=2 ! 0 ! 1=2 in the form er work, whereas a possible triplet ground state for two added electrons was suggested by the latter authors, i.e. the sequence S = 0 ! 1=2 ! 1! 1=2.

Here we focus on CVD-grown metallic carbon nanotubes $(CNTs)^{12,14}$ W e will rst exam ine the four-fold shell pattern in great detail and demonstrate that the half-led ground state (i.e. 2 electrons added to an empty shell) is either a paired electron with S = 0 or the six possible two-electron states are electively degenerate due to a level broadening exceeding the orbital mism atch and exchange energy. W electron we have discovered striking gaps in several samples. This anom ally is at present not understood.

II. EXPERIMENTAL

Single wall carbon nanotubes (SW NTs) have been grown from patterned catalyst islands by the chem ical vapor deposition m ethod on Si/SiO_2 substrates.¹⁵ The degenerately doped silicon, term inated by a 400 nm thick SiO_2 layer, is used as a back-gate to m odulate the electrochem ical potential of the SW NT electrically contacted with a source and drain term inal. The contacts are patterned by electron-beam lithography (EBL) using polym ethylm ethacrylate (PMMA) as resist, followed by m etallization with palladium and lift-o $.^{14,16}$ O noe the samples are made, sem iconducting and m etallic SW NTs are distinguished by the dependence of their electrical conductance G on the gate voltage V_g m easured at room tem perature (T 300K).¹⁴ In the rest of the paper we report on m easurem ents perform ed on m etallic SW NTs with relatively low-ohm ic contacts, such that co-tunneling and K ondo physics is observable.

The electrical characterization of the devices has been performed at low temperature in a ³He system at 300 mK. We measure the electrical current I with a low noise current to voltage amplier as a function of source-drain (V_{sd}) and gate (V_g) voltage and determine the di erential conductance $G_d := @I=@V_{sd}$ num erically. Finally, the collected data $G_d(V_{sd};V_g)$ are represented in a two-dimensional grey-scale representation in which the grey-scale corresponds to the magnitude of G_d . The linear-response conductance $G := I=V_{sd}$ with V_{sd} ! 0 is measured at a small but nite source-drain voltage of 40 V.

III. RESULTS AND DISCUSSION

In this section, we will focus rst on one set of measurements which we will analyze in great detail. This set of data is shown in Fig. 1. Fig. 1a shows the linear-response conductance G as a function of gate voltage V_g . Fig. 1b and 1c display the corresponding grey-scale plots of the dimential conductance G_d in zero magnetic end and B = 5T, respectively. White corresponds to low and black to high conductance.

The observed patterns correspond to a quantum dot with a relatively strong coupling to the contacts. Signatures of the latter are high conductance 'ridges', observed at zero bias ($V_{sd} = 0$) and B = 0, caused by the the K ondo e ect. This e ect is a many-electron e ect and requires a relatively high tunneling coupling to the leads in order to be appreciable at tem peratures where the m easurem ents take place. As required,^{5,6} we indicate the formation of the leads in the leads tem perature is low ered below. As required,^{5,6} we indicate the perature close to the unitary limit of $G = 2e^2 = h$. The characteristic energy scale, i.e. the K ondo tem perature T_K , has been deduced from the tem perature dependence of G in ridge 3 (not shown) and found to be $T_K = 2K$. The conductance enhancem ent due to the K ondo e ect is observed at zero source-drain voltage if B = 0. In a magnetic eld, how ever, the conductance enhancem ent is

reduced and a splitting of the peak conductance to nite source-drain voltages is expected.^{5,18} This splitting is visible in Fig. 1c which was measured in a perpendicular magnetic eld of 5T. That the linear-response conductance G is suppressed in a magnetic eld is clearly seen in Fig. 1a in which the solid (dashed) curve correspond to B = 0 (B = 5T).

Because the many-electron e ects (K ondo e ect) are suppressed in magnetic eld, we can use the linear-response conductance measurement in magneticeld (dashed curve in Fig. 1a) to assign the charge states of the quantum dot with reference to the single electron tunneling picture. A transition from a ground state with N electrons in the dot to one with N + 1 gives rise to a peak in the conductance, whereas G is suppressed in between. This pattern is nicely seen in the dashed curve of Fig. 1a, in which transitions have been labelled. Evidently, these conductance peaks form a repeating pattern in clusters of four. This pattern is the generic shell pattern of an ideal CNT quantum dot.^{11,13} It is caused by the four-fold degeneracy of Od-eigenstates, two of which stem from spin and the other two from the so-called K K⁰ orbital-degeneracy of graphene.¹ The four-fold pattern can be regarded as a measure of the quality of the SW NTs. It is not observed in all SW NTs and even if observed it is not usually present over the whole gate voltage range. But it can repeat over several shells, not just two as shown in Fig. 1. The degeneracy may be lifted by disorder and by the contacts which m ay couple di erently to the two orbital states. As has been pointed out be 0 reg et al., the four fold pattern m ay be absent even in a 'perfect' SW NT because the two orbital states can respond di erently to the electrostatic gate-eld if inhom openeous.¹⁹

Let us continue to analyze our data in term s of the constant-interaction m odel.²⁰ In order to assign the states only two parameters are needed: the single-electron charging energy $U \coloneqq e^2 = C$ (which can be expressed by the total capacitance C and is assumed to be a constant in this m odel) and the single-electron level spacing E. Note, that E m easures the energy di erence between a led shell to a state with one additional electron. This is sketched in the inset of F ig. 1a. To add an electron one has to provide an addition energy' composed of charging energy U plus level-spacing E, the latter only if the electron m ust be added into a new shell. Therefore, the addition energy E equals E + U for the rst electron in a shell, whereas it amounts to bn ly' U for the follow ing three added electrons belonging to the same shell. Since E is proportional to the gate-voltage di erence between adjacent conductance peaks (the conversion factor equals $e_g = C$), the labelling of states

in terms of charge N in Fig. 1a should be understandable. $N = 0 \mod 4$ corresponds to a ground state with a lled shell. Due to the large addition energy, the conductance is strongly suppressed for a lled shell, giving rise to the diam ond-like white areas (denoted by A, B and C) in the grey-scale plots. Adding electrons to the lled shell one by one (peaks in G, dashed curve of Fig. 1a), we reach the state N = 4 which corresponds again to a lled shell.

In the following, the ground states will be labelled by N = 0:::3 for the rst quartet and N = 0° :::3° for the second, where N = 4 = 0°. Relying on the constant interaction model, the ratio between the average level spacing and charging energy amounts to E =U 1 in our data. It is seen, however, that U is constant to a good approximation, but that E varies. For the respective diamonds A, B and C, the level spacing E amounts to 7, 5, and 3m eV, respectively. Theoretically, the level-spacing of an ideal SW NT is given by E = hy = 2L, where $v_F = 8$ 10⁵ m/s is the Ferm i velocity and L the length of the tube that determines the 1d cavity.¹ Taking the nanotube length L measured from the edges of the contacts, which for this sample amounts to L 300 nm, the equation predicts a level-spacing of E 5.5m eV in good agreement with the experimental values of 3 7m eV. The data in Fig.1 yields for the charging energy U = 5.3 0.5m eV and a gate-conversion factor of $\approx C_q=C$ of 0.08.

Focusing on the high-conductance K ondo ridges at zero bias voltage, we see in Fig. 1b a ridge at charge states N = 1 and N = 3, whereas G is suppressed at half-lling, i.e. at N = 2. The situation is di erent for the second quartet, where K ondo ridges are observed for all three states N = 1, 2 and 3. This phenom enon was reported before by Liang et al.¹³ W hereas a spin-1=2 K ondo e ect is expected for N = 1 (one electron) and N = 3 (one hole), the situation at half-lling, i.e. at N = 2 is less obvious. The observed K ondo-e ect was assigned to a spin-1 triplet state in Ref.¹³. In the following we re-exam ine this assignment. To do so, we have to go beyond the Yiree' electron m odel and consider am ong other things the exchange interaction. There are three additional parameters: F irst, it has been pointed out that the orbital degeneracy need not to be exact.^{11,13} The orbitalm ism atch is denoted by . W ith regard to on-site charging energy the doubly occupancy of one orbital is a bit higher in energy as compared to placing each of the two electrons in a separate orbital. This parameters has been introduced by 0 reg et al.¹⁹ and is denoted by U. Finally, placing the two electrons in di erent orbitals gives rise to a spin-dependent exchange energy term , which according to H und's rule favors the triplet state, i.e. the state with spin S = 1. This parameter is denoted by J. These parameters have been extracted, both for MWNTs¹¹ and SWNTs¹³ and the analysis of our data conm the previously obtained values. The importance of the parameters in descending order is , J and U as the least important one. The former work by Buitelaar et al. reports 0.2 and J < 0.09 and the latter work by Liang et al. reports 0.3, J 0.1 and U < 0.1 (all numbers are measured in units of level spacing E). We neglect U because it is small and typically much smaller than the bare level broadening , which - as we will emphasize - matters as well. Since the K ondo e ect is the dynamic screening of the local spin by exchange with a sea of electrons, it is tempting to assign the K ondo ridge for N = 2 to a spin-1 (triplet) ground state. However, with regard to the just mentioned parameters, this appears to be unlikely, because J < , favoring a spin-0 ground state.¹⁹

Let us rst contrast the possible states at N = 1 and N = 2 for the case of degenerate orbitals (=0) and without exchange (J=0), shown in Fig. 2a, with the case of a nite level mismatch and a nite exchange energy, shown in Fig. 2b. In the rst (maybe too naive) m odel of Fig. 2a, the degeneracy equals 4 at N = 1 and clearly K ondo physics can em erge. At N = 2 the degeneracy is even larger, am ounting to 6 and second-order elastic spin-ip processes are energetically allowed so that K ondo physics can emerge as well. Here, two states are paired-electron states and the other four may be labelled as one singlet state with spin S = 0 and three triplet states with S = 1, denoted as S and T states. The K ondo e ect m ay be expected to be even enhanced in this case due to the larger number of states.²¹ This scenario corresponds to the K ondo e ect for which the singlet and triplet states are degenerate. This has been realized experimentally in sem iconducting quantum dots by tuning the states with either a magnetic or an electric eld.^{21,22,23} Once we go over to the more realistic model shown in Fig. 2b, assuming that exchange and level mism atch are non-zero and of com parable m agnitude, the N = 1 states remains horm all in the sense that only the lowest lying orbital need to be considered. At half-lling, i.e. at N = 2, there are however two possibilities:¹⁹ if exchange dom inates (J >), the ground state is the spin triplet (T) state, whereas if the opposite holds, the ground state is a paired electron (PE) residing on the lowest orbital state. The energy di erence between the T and PE states is J.²⁴ Although the Kondo e ect is (in principle) possible for the triplet, given by = there is no K ondo e ect possible for paired electrons. N ote, that unlike previous discussions, there are three cases to consider at half-lling. Two may give rise to K ondo and one does

not. To have an abbreviation at hand we denote the three N = 2 states with ST (degenerate ground state), PE (paired electron ground state) and T (triplet ground state). A sm entioned above, the K ondo ridge at N = 2 has been assigned to the triplet state.¹³ Though this is tempting at rst sight, there is no necessity. In fact, this assignment is unlikely, rst because J is measured to be small (usually smaller than) and secondly, the K ondo temperature T_K for triplet K ondo is predicted to be much smaller than T_K for S = 1=2-K ondo²⁵ (an estimate will follow below).

We now look at the excitation spectra for N = 1; 3 and N = 2 in zero eld. This is shown in Fig. 3 (a-c), where (a) and (b) correspond to odd $\lim_{n \to \infty} (N = 1;3)$ and (b) to half- $\lim_{n \to \infty} (N = 1;3)$ (N = 2). The energy of the rst excited state at xed N relative to the ground state is given by the level m is match , both for N = 1 and N = 3, i.e. 13 = 3. This is illustrated in the respective insets on the right. The rst excited states show up as a conductance peak at nite V_{sd}, corresponding to the excitation energy. This is a so-called inelastic cotunneling process. We obtain from the measurement $_1 = 0.92 \text{ meV}$ and $_3 = 0.85 \text{ meV}$. Hence, the level m is match is given by $0.89 \quad 0.4 \text{ meV}$. For the N = 2 case we have to distinguish two possibilities: if J > -, the ground state is the triplet (T) and the excited state the paired electron (PE) state, yielding $_2 = J$. If on the other hand J < , the states are reversed, yielding $_2 = J$. In general, $_2 = j$ Jj. From the experiment (Fig. 1c) we deduce $_2 = 0.38 \text{ meV}$. We stress that we measure on one and the same shell so that we can use the parameter , measured for the N = 1;3 case, also for the N = 2 case. Com paring the num bers, leaves open two possibilities: either the exchange param eter is quite small, i.e. J 0 (taking the possible errors into account J. 0:1meV), or it is quite large J & 1:65 m eV. If the latter would be true, it would be a rem arkable coincidence that we nd j JΪ with J 2. Moreover, the ratio J = E > 0.3 would be quite rem arkable with regard to previous measurements. On the other hand, comparable values for J have theoretically been predicted, how ever only for sm all diam eter tubes. For example, J = E was estimated to be 0:22 and 0:44 for a (10;10) and (5;5) tube, respectively.¹⁹ However, the diam eter d of CVD -grown NTs is known to vary substantial and in particular we nd that d & 2 nm,¹⁴ from which one would theoretically predict an exchange parameter of order J= E 0:1, which disagrees with the nding above. If J were indeed as large as 2, and therefore J >, the triplet state would be the ground state at half-lling, i.e. at N = 2 and $N = 2^{0}$. The K ondo e ect at half-lling must then be assigned to the S = 1

K ondo e ect. To explain the absence of the K ondo e ect for N = 2 and its presence for N = 2⁰, one would have to argue that the K ondo temperature is smaller than 300 m K at N = 2, whereas it is larger at N = 2⁰. Pustilnik et al.²⁶ showed that the K ondo temperature $T_{K}^{S=1}$ for the triplet state is smaller than $T_{K,l=2}$ for the spin-1=2 case. M ore precisely, $T_{K,l}$ can be estimated according to $k_{B}T_{K,l} = k_{B}T_{K,l=2}^{2} = E$. The average width of the zerobias resonances at N = 1;3 in the left quartet is measured to be 0.35 m eV, yielding as a prediction $T_{K,l} = 0.25$ K. In the right quartet the same procedure yields for N = 1⁰;3⁰ a mean width of 0.8 m eV, from which one predicts $T_{K,l} = 1.5$ K. Hence, the comparison with the measuring temperature does not exclude S = 1 K ondo, as $T_{K,l} = 0.3$ K in the right one. However, the ratio $T_{K,l} = T_{K,l=2}$ measured in the right quartet is inconsistent with theory which predicts $T_{K,l=2} = E$. The form er is evaluated to 0.8 :::1.6, whereas the latter is at most 0.3. In simple terms, the appearance of the two resonances at N = 1⁰ and N = 2⁰ with essentially one and the sam e width (1.1 and 0.9 m eV, respectively), makes triplet-K ondo quite unlikely.

In magnetic eld the states further split due to the Zeem an energy given by $g_B B = 2$, where B is the Bohrm agneton and g the so-called g-factor. g has been m easured in related electrical measurements on carbon nanotube quantum dots and found to agree with the free electron value of $g = 2^{3,11,27}$ Due to the Zeem an-splitting the excitation spectrum changes. At N = 1 and for sm all m agnetic elds (with regard to the level m ism atch), the spin-1=2 K ondo resonance is expected to $split_{r}^{11}$ evolving into inelastic co-tunneling with an excitation energy given by $z = g_B B$. Because of the relatively large width of the zero-bias resonances, this shift is hardly visible for small magnetic elds in the experiment. That is why we have chosen a relatively large eld of 5T. This eld yields for the Zem ann excitation energy 0.58 meV, taking $q = 2.0 \text{ ote, however, that there is a second excited state given by$ the level m ism atch 0:9m eV. If we analyze the non-linear di erential conductance as a function of V_{sd}, we see two excitation lines (one at positive and one at negative bias), which are markedly broadened, suggesting an overlap of two excitation features, see Fig. 3a (grey overlaid graph). The onset of the excitation peaks agrees with the Zeem an energy (arrows from below). This analysis is of particular in portance in the N = 2 case, because it allows us to distinguish the PE from the T ground state unam biguously, see Fig. 4. If the ground state is the paired-electron state, the rst excitation occurs at energy $_2 =$ J Ζ

 $_{\rm Z}$ (because J $\,$ 0) and the second lies at $\,$. In contrast, if the ground state is

the spin-1 triplet state the nst two excited states have energy $= J + _z + _z$ and $J + _z 2 + _z$ (because J 2 in this case). This is shown (approximately to scale) in the illustrations of Fig. 4b and c, respectively. Based on the eld-dependence of the excitation spectrum we can predict the position of the excitation peaks for the two cases. In the measurement, shown in Fig. 4a, the upper black arrows point to expected excitations if the ground state is the paired-electron (PE) state, whereas the upwards pointing open arrows correspond to the expected excitations for the triplet (T) ground state. It is obvious that the agreement with the PE state is much better. The excitation peaks at zero eld do not move out to larger energies expected for the T ground state, but rather shrink. In particular there are clear low energy shoulders visible which agree quite reasonably with the expected low est energy excitation energy for the PE ground state.

Taking all argum ents together, this makes a convincing case for the ground state at halflling, i.e. for N = 2, which is the paired-electron state. Moreover, the exchange energy m ust be very sm all. How do we then have to explain the pronounced K ondo ridge at N = 2° , visible in Fig. 1b? A swe have pointed out when discussing Fig. 2, there are two cases at half-lling that allow for K ondo: spin-1 K ondo in case of the triplet state or the degenerate ground state, i.e. the ST -state. Based on our previous discussion the form er can be excluded, so that the only remaining possibility requires degenerate orbitals. We know that the orbitals are not exactly degenerate. The level m ism atch, as deduced from the N = 13 states, am ounts to 0:9m eV, which is quite appreciable. Due to the relative large width of the zero-bias conductance peaks at $N = 1^0 ::: 3^0$ we are not able to deduce the level m ism atch on the second shell along the same lines as before for the rst shell. Though it is possible is smaller in the second shell, it is unlikely zero. We emphasize, however, that it is that crucial to compare the level m ism atch with the level width, due to the tunneling couplings $_{\rm s}$ and $_{\rm d}$ to the respective contacts. If < , where = $_{\rm s}$ + $_{\rm d}$, the two orbital states cannot be distinguished and are in e ect degenerate. We know from other measurements on carbon nanotubes that may vary a lot with gate voltage. Our picture of the half-led state is correct, if we can show that is smaller than within the rst shell, but larger within the second. There are several ways to deduce . One possibility is to deduce it from the width of the excitation features at xed N, another one is to analyze the transitions at nite bias at the edge of the Coulom b-blockade (CB) diam onds. For the left shell the excitation spectra for states N = 2 and N = 3 (see Fig. 3) yield 0.7 m eV, whereas

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a cut at $V_g = 3:1V$, corresponding to the transition 0 \$ 1, yields 0:9m eV. Because we cannot resolve excitation features in the right shell, we have to rely on transitions at the edge of CB-diam onds. We deduce $3m eV at 0^0 \$ 1^0$ and $1:9m eV at 3^0 \$ 4^0$. Clearly . for the left shell and > for the right one in support of our statem ent. To conclude this part, we can say that the K ondo e ect at $N = 2^0$ is not a triplet K ondo, but arises because is larger than the level m ism atch, resulting in a ground state in which the paired-electron, the singlet and triplet states are electively degenerate. Our data is only consistent with a very sm all exchange exchange term of J = E = 0.022. Such a sm all value can only be reconciled with theory¹⁹ if either the tube has a large diam eter of order 10 nm or the interaction is locally screened, possibly by the presence of other nanotubes form ing a bundle.

Exam ination of the measured data shows that for the K ondo resonances labelled with 1^0 and 3⁰ in Fig. 1b, the positions of the maximum conductance are situated at non-zero bias. This is shown in Fig. 5. This phenom enon has been observed in sem iconducting quantum dots and was term ed the anom alous K ondo e ect by Simmelet al.²⁸ It was suggested by these authors that the e ect is due to asymmetric and energy-dependent coupling strengths s and d to the two reservoirs. The e ect has thereafter been con med theoretically in a singlein purity Anderson model.²⁹ The authors show that the peak conductance is shifted provided that $_{s} \in _{d}$, but an energy dependence of $_{s:d}$ is not required. We stress here, however, that the Anderson model introduces an additional model-dependent asymmetry in that U ! 1 , which is not realized in a real quantum dot. At half-lling, there is particle-hole symmetry where electrons (holes) can be exchanged via both the bare state at energy $_{0}$ and the one at $_0$ + U. In this case, no shift of the K ondo peak is expected even if $_s$ ϵ d. Extrapolating G (I) to the unitary limit G (0) at zero tem perature (not shown) using the standard expression to t the K ondo e ect, i.e. $G(T) = G(0) = 1 + (2^{1-s} - 1)(T = T_K)^{2} \int_{0}^{2} we obtain$ for the ridge at charge state N = 3 a zero tem perature conductance of G (0) = 1:68 $e^2 = h_r$ out of which the ratio is estimated to be 2. Hence, there is an asymmetry of magnitude com parable to Ref.²⁸. Our statement, that the shift of the K ondo peak to nite bias is absent at half-lling is beautifully relected in the data of Fig. 5. Due to the four-fold symmetry, half-lling corresponds to charge state $N = 2^0$ and indeed, this peak has its maximum at $V_{sd} = 0$. The other two resonances are shifted oppositely, one to $V_{sd} > 0$ (N = 1⁰) and the other to $V_{sd} < 0$ (N = 3⁰). The shift amounts to 0.22 m eV. These shifts are comparable in

m agnitude to the ones seen by Schimmel et al., although they have observed only unipolar shifts. Finally we remark that the transitions to the Coulomb-blockade diam onds, i.e. 2^{0} \$ 1^{0} and 3^{0} \$ 4^{0} are asymmetric with respect to the V_{sd}, see arrows. Cross-sections at constant gate-voltage through these transitions allow to deduce the respective 's and their ratio: = s = d. We point out, that this asymmetry is a consequence of the level degeneracy. Consider tunneling at nite bias into the N = 1^{0} state. Because there is a four-fold degeneracy the elective in-tunneling rate is enhanced by a factor of 4. In contrast, this phase-space argument does not hold for the out-tunneling rate. The respective current steps are then given by (4e=h) s d=(s + 4 d) for one bias polarity (e.g. $V_{sd} > 0$) and (4e=h) s d=(4 s + d) for the other polarity, where the factor 4 counts the degeneracy. It is clear from these two relations that the current steps are only dilement for the two polarities if 6 1. The two current steps, measured for the transition 3^{0} \$ 4^{0} , am ount to 20 and 30 nA, yielding for the -ratio 2 (in agreement to what we have deduced before in a

di erent way) and $_{\rm s}$ 1:4 m eV and $_{\rm d}$ 0:7 m eV, so that the total level broadening is approximately 2 m eV. A loo the latter value is in agreement with the previously mentioned width of the transition, which we measured to be 1:9 m eV.

A fter this extensive analysis we use the last part of this section to point to observed deviations. Fig. 6 displays the dependance of the linear-response (a) and di erential conductance (b) of another sample also contacted with Pd. The contact separation is longer and am ounts 0.8 m. The linear-response conductance is bound by $2e^2$ =h suggesting that we meato L sure through one individual SW NT. Four-fold clustering in the electron addition spectrum is observed form one then ve shells (A E), corresponding to 20 electrons. Due to the three tim es larger length of this device as compared to the one in Fig. 1 the energy scale is reduced by approximately a factor of three. The level-spacing amounts to E 1 1:5m eV and the charging energy to U 1 meV. The ratio E=U 1 as before. As with the data of Fig. 1 the K ondo e ect m ay appear at half-lling () or m ay be absent (), which according to the discussion above would correspond to the PE and S ground state, respectively. There are di erences, however. The most dram atic one occurs in shell D for the three electron state ($\lim_{x \to \infty} 3=4$), m arked with 0. Instead of the expected spin-1=2 K ondo, the conductance is actually suppressed. This is seen as a pronounced white bubble. Because the K ondo e ect is present for the one electron state ($\lim_{n \to \infty} 1=4$), this in plies breaking of particle-hole sym metry. This e ect is quite surprising and has not been reported before. We do not have

a convincing explanation but mention one possibility. The three electrons at N = 3 m ay like to form a high-spin state with total spin S = 3=2. However, this requires three di erent orbitals, but there are only two in an ideal tube. It may be that the nanotube is not perfect, rather a bundle or a multi-shell tube, which may provide additional orbitals. We think that this scenario is unlikely, because we just have shown that the exchange is small, and it is particularly small if the interaction is screened by other tubes. The gap may however be induced by a magnetic defect caused by residual catalyst particles, which may enhance the exchange energy. Due to the small size of catalyst particles such a defect interacts only beally. If e cient, one would expect a strong e ect on the addition energy due to the large energy scale of the defect. In our opinion, the observed regularity of the addition pattern rules out disorder.

Sim ilar gap-features are som etim es seen over the entire grey-scale plot. W e show in Fig.7 a short section taken out of an extensive di erential conductance grey-scale plot of another sample. The contacting material is Au in this case and the contact separation amounts to 1 m. The contact transparencies are lower here and typical two term in al conductances L are of order $0:1e^2=h$. Consequently, the main features in the di erential-conductance are Coulomb blockade (CB) diamonds. The generic four-fold shell structure is not apparent. It is masked by the charging energy which dom inates here. The observed addition energy amounts to E 5 m eV. We stress that the dI=dV _{sd} measurem ents of Fig. 7a extend over more than 17 electrons without any noticeably change. The linear response conductance (Fig. 7c) shows a very regular set of high conductance peaks at the transition between neighboring charge states with peak values approaching $0.8e^2$ =h. The spacing between these CB-oscillation peaks is surprisingly constant, amounting to $V_q = 73$ 5mV. This yields a gate-coupling constant of = 0.068, which is comparable to the one deduced for the sample of Fig. 1 (= 0.08).

W e present this m easurem ent here, because of the presence of a striking gap-structure, which is seen inside of all CB diam onds and which m ight be related to the gap which we have m entioned before, i.e. the feature labelled 0 in Fig. 6b. Two dI=dV_{sd} cross-sections at constant V_g are presented in Fig. 7b. W e nd that the size of the gap $_g$ varies a bit in di erent charge state and is estimated to be $_g$ 0:7m eV (0:3:::0:9m eV). Additional suppression m ay be caused, if the nanotube is split by a strong scattering center into two segments in series. In this case, however, a regular periodic CB-oscillation pattern is not

expected, because single electron transport requires that two charge states are degenerate in both segments simultaneously. While this maybe possible occasionally, it would be surprising if the levels would move in both segments with gate voltage exactly equally. We therefore are convinced, that this scenario is wrong. A loo a possible parallel conductance through two (or more) di erent tubes can be excluded, because this should appear in the greyscale-plot as a bare superposition of two CB-patterns. Moreover, the observed grey-scale plot cannot be modelled as a regular CB-pattern multiplied by a gap-feature in the vicinity of V_{sd} 0. This is evident from the Fig. 7c which shows G (V_q) at $V_{sd} = 0$ (full curve) and at $V_{sd} = 1.5 \text{ mV}$ (dashed curve). In the shaded region, corresponding to Fig. 7a, the suppression is only active in between the CB-oscillation peaks, whereas the peaks them selves are not suppressed, suggesting that the Od orbitals extend from source to drain. The lowconductance bubbles' are therefore con ned to the CB-region of the nanotube and this new e ect is observable in transport through a single carbon nanotube. This does not mean that there is only one single walled carbon nanotube present. The device m ay still consist of a sm all bundle or a multishell tube, of which only one tube is e ectively coupled to the reservoirs. In addition, the presence of magnetic in purities in the form of catalyst particles cannot be excluded, so that the observed gaps may originate from magnetic interactions with these particles. The K ondo e ect which results in a high conductance resonance can be described as an anti-ferrom agnetic exchange between the leads and the quantum dot. It is tem pting to suggest that the opposite scenario, namely ferrom agnetic exchange with, for exam ple, a m agnetic particle, m ay suppress the conductance.³¹

IV. CONCLUSION

In conclusion, we have analyzed the ground-state of carbon nanotubes which are relatively strongly coupled to the attached leads. Spin 1=2 K ondo is present for charge states N = 1 and N = 3. At half-lling, i.e. for two electrons on the dot, the ground-state is either a non-degenerate paired electron or a highly degenerate two-electron state. W hereas the K ondo e ect is prohibited in the rst case, it is allowed (and enhanced) in the second. The appearance of the K ondo e ect at N = 2 is largely determ ined by the magnitude of the level broadening , caused by the coupling to the leads. W e have also observed striking gaps whose origin need to be unravelled in the future.

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FIG.1: (a) Linear response conductance G as a function of back-gate voltage V_g of a SW NT device with contact separation L 300 nm (edge-to-edge of reservoirs), measured at T = 300 m K and in a magnetic eld of B = 0 (solid curve) and B = 5T (dashed curve). A clear clustering in four peaks is observed (pronounced in magnetic eld), which suggests a single-electron shell pattern with four-fold degeneracy. Charge states corresponding to a lled shell (inset) are labelled as 0 or 4. (b,c) C orresponding grey-scale plots of the di erential conductance dI=dV_{sd} (darker m ore conductive) at B = 0 (b) and B = 5T (c) as a function of gate V_g and source-drain voltage V_{sd}. In the rst shell, high conductance K ondo ridges (visible at V_{sd} 0) are observed for charge states 1 and 3, whereas they appear for states 1^0 , 2^0 , and 3^0 in the second shell. The K ondo ridges clearly split in the applied magnetic eld.

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FIG.2: Illustration of the state- lling scheme for one (N = 1) and two (N = 2) excess electrons. In (a) the level-m ism atch and the exchange energy J are zero, whereas these parameters are non-zero in (b). PE denotes a paired-electron state, S (T) the singlet (triplet) two electron state. The K ondo-e ect m ay arise in three cases: obviously for the spin-1=2 with one excess electron (N = 1) and if N = 2 for the spin-1 triplet state, but also for the case for which = J = 0, i.e. when the singlet and triplet states are degenerate (ST state).

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FIG.3: Non-linear di erential conductance $dI=dV_{sd}$ as a function of V_{sd} at $V_g = const deduced$ from the data shown in Fig. 1b at zero magnetic eld. (a) and (b) correspond to the states N = 1and N = 3, whereas (c) correspond to the half-lied shell N = 2. All three $dI=dV_{sd}$ cuts have been placed in the middle of the charge state. The visible excitation peaks occur at energy and are due to inelastic co-tunneling through the excited state. The relevant states are illustrated in the respective insets on the right. The grey curve in (a) has been measured in a magnetic eld of 5T. A rrow spoint to $_{Z} = g_{B}B = 0.58 \text{ m eV}$ using g = 2.

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FIG. 4: (a) Non-linear di erential conductance $dI=dV_{sd}$ as a function of V_{sd} taken from the data shown in Fig. 1b at a xed gate-voltage corresponding to N = 2. The thick (thin) curve was measured in a magnetic eld of B = 5T (B = 0T). (b) and (c) illustrate the magnetic-eld dependence of the rst two excited states at N = 2. The two cases are drawn approximately to scale using the fact that J is either 0 (PE ground state) or 2 (T ground state) deduced from the data of Fig. 1 and Fig. 3.

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FIG. 5: The K ondo resonance is observed to be o set with respect to the bias voltage V_{sd} for the mixed-valence state with lling 1=4 (N = 1⁰) and 3=4 (N = 3⁰), whereas it is centered at $V_{sd} = 0$ at half-lling. (a) shows the respective di erential conductance at constant gate voltage corresponding to part (b), which reproduces the second shell of Fig. 1b. A rrows emphasize an additional asymmetry, discussed in the text.

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FIG. 6: (a) Linear response conductance plotted as a function of the gate voltage V_g and (b) di erential conductance dI=dV_{sd} (darker m ore conductive) plotted as a function of V_g and V_{sd} for an another SW NT device with length L 800 nm contacted by palladium. The shell pattern of four electrons each extends over 5 shells (A E). The K ondo e ect occurring at half-lling is m arked with , while corresponds to the singlet ground state. O points to an anom aly, a strong gap-feature arising for a three electron state. The non-linear dI=dV_{sd} through the m iddle of this state is shown in (c).

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FIG.7: (a) D i erential-conductance plot of a SW NT device with contact separation L 1 m at T = 300 m K (m aximum conductance = e^2 =h, black). C oulom b blockade diamonds are clearly seen. In addition gaps appear near zero bias. (b) dI=dV_{sd} as a function of V_{sd} and at constant V_g along the corresponding lines, shown in (a). C onductance as a function of gate voltage taken at V_{sd} = 0 (full) and V_{sd} = 1.5 mV (dashed). The shaded region correspond to (a).